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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	. ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/550,643	09/23/2005	Kunihiko Iwamoto	PRM-0052	1946
23413 CANTOR COL	590 06/28/2007 BUDNI I D	·	EXAMINER	
CANTOR COLBURN, LLP 55 GRIFFIN ROAD SOUTH BLOOMFIELD, CT 06002			RODELA, EDUARDO A	
			ART UNIT	PAPER NUMBER
			2826	
			MAIL DATE	DELIVERY MODE
•			06/28/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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		Application No.	Applicant(s)				
		10/550,643	IWAMOTO ET AL.				
	Office Action Summary	Examiner	Art Unit				
	·	Eduardo A. Rodela	2826				
Period fo	The MAILING DATE of this communication apport	pears on the cover sheet with the	correspondence address				
WHIC - Exte after - If NC - Failt Any	ORTENED STATUTORY PERIOD FOR REPL CHEVER IS LONGER, FROM THE MAILING D insions of time may be available under the provisions of 37 CFR 1.1 r SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory period are to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailin led patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATIO (36(a). In no event, however, may a reply be to will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDON	N. mely filed nthe mailing date of this communication. ED (35 U.S.C. § 133).				
Status							
1)⊠	Responsive to communication(s) filed on 18 A	pril 2007.					
2a) <u></u> □	This action is <b>FINAL</b> . 2b)⊠ This action is non-final.						
3)[	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
	closed in accordance with the practice under the	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.				
Disposit	ion of Claims						
4)⊠	Claim(s) <u>1-8</u> is/are pending in the application.						
	4a) Of the above claim(s) is/are withdra	wn from consideration.					
5)⊠	Claim(s) 7 is/are allowed.						
6)⊠	Claim(s) <u>1-5 and 8</u> is/are rejected.						
•	Claim(s) <u>6</u> is/are objected to.						
8)[	Claim(s) are subject to restriction and/o	or election requirement.					
Applicat	ion Papers						
,	The specification is objected to by the Examine						
10)⊠	The drawing(s) filed on $9/23/05$ is/are: a) $\boxtimes$ ac	ccepted or b) objected to by th	e Examiner.				
	Applicant may not request that any objection to the	drawing(s) be held in abeyance. Se	ee 37 CFR 1.85(a).				
	Replacement drawing sheet(s) including the correct						
11)[	The oath or declaration is objected to by the E	xaminer. Note the attached Offic	e Action or form PTO-152.				
Priority	under 35 U.S.C. § 119						
•	Acknowledgment is made of a claim for foreign ☑ All b) ☐ Some * c) ☐ None of:		a)-(d) or (f).				
	1. Certified copies of the priority documen						
	2. Certified copies of the priority documen		<u>-                                    </u>				
	3. Copies of the certified copies of the price	•	ed in this National Stage				
*	application from the International Burea See the attached detailed Office action for a list		her				
	See the attached detailed Office action for a list	of the certified copies not receive	eu.				
Attachme	nt(s)						
	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948)	4) Interview Summar Paper No(s)/Mail [					
3) 🔯 Info	ce of Draftsperson's Patent Drawing Review (P10-948) mation Disclosure Statement(s) (PTO/SB/08) er No(s)/Mail Date <u>9/23/05 and 5/22/06</u> .	5) Notice of Informal 6) Other:					

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## **DETAILED ACTION**

This Office Action is in response to the Applicant's Arguments submitted April 18, 2007.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-3 and 8 are rejected under 35 U.S.C. 102(e) as being anticipated by Li (US 2005/0280104).

Regarding claim 1, Li shows in Figure 10, a semiconductor device comprising: a semiconductor substrate [202];

a gate insulating film [GD] formed on the semiconductor substrate [202]; and a gate electrode [G] formed on the gate insulating film [GD],

wherein the gate insulating film is a layered film including a plurality of nitrogen-containing metal compound layers having nitrogen atoms [paragraph 0037,0038]. It is noted that the limitations of the gate insulating film having nitrogen atoms being "diffused therein" is considered to be a process limitation that carries no patentable weight because the current claim is directed to a device structure, therefore a "product

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by process" claim is directed to the product, and no matter how the structure is actually made, it is the final product which must be determined in a "product by process" claim, and not the patentability of the process. The presence of process limitations on product claims, which product does not otherwise patentably distinguish over prior art, cannot impart patentability to the product. *In re Stephens 145 USPQ 656 (CCPA 1965)*.

Regarding claim 2, Li shows in Figure 10, Li shows in Figure 10, the semiconductor device according to claim 1, wherein the plurality of nitrogen-containing metal compound layers each contain an element selected from the group consisting of Hf, Zr, and Si [paragraph 0038].

Regarding claim 3, Li shows in Figure 10, a semiconductor device comprising: a semiconductor substrate [202];

a gate insulating film [GD] formed on the semiconductor substrate [202]; and a gate electrode [G] formed on the gate insulating film [GD],

wherein the gate insulating film [GD] is a layered film including a plurality of nitrogen-containing metal compound layers having different nitrogen compositions (1 - q), expressed by the following equation,  $M_PM'_{1-p}O_qN_{1-q}$  where 1 >= p >= 0, 1 > q >= 0, and M and M' each represent an element Hf [paragraph 0038].

Regarding claim 8, Li shows the semiconductor device according to claim 1, wherein the layered film is formed by atomic layer deposition [paragraph 0045].

Claims 4 and 5 are rejected under 35 U.S.C. 102(e) as being anticipated by Lim et al. (US 2007/0001241).

Regarding claim 4, Lim shows in Figure 7, a semiconductor device comprising:

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a semiconductor substrate [53];

a gate insulating film [63,65,67] formed on the semiconductor substrate; and a gate electrode [71] formed on the gate insulating film [63,65,67], wherein the gate insulating film is a layered film including:

a first metal compound layer containing a metal compound expressed by the chemical formula  $M^{1}O_{x}N_{1-x}$  [paragraph 0011];

a second metal compound layer formed on the first metal compound layer, containing a metal compound expressed by the chemical formula  $M^2O_yN_{1-y}$  [paragraph 0010]; and

a third metal compound layer formed on the second metal compound layer, containing a metal compound expressed by. the chemical formula  $M^3O_zN_{1-z}$ , [paragraph 0011];

where  $1 \ge y > x \ge 0$ ,  $1 \ge y > z \ge 0$ , and M1, M2, and M3 each independently represent an element selected from the group consisting of Hf, Zr, La, Al, Si, and Y [paragraph 0010,0011].

Regarding claim 5, Lim shows the semiconductor device according to claim 4, wherein:

$$1 > Y > X > 0$$
 and  $1 > Y > Z > 0$  hold; and

each of the first, second, and third metal compound layers is one selected from the group consisting of a metal oxynitride layer and a metal nitride layer [paragraphs 0010,0011].

## Allowable Subject Matter

concentration of nitrogen in the dielectric layers.

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Claim 6 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. The prior art does not show the specified

Claim 7 is allowable since the prior art of record does not show the relationship between the 'r' and 's' values being non-integer values in conjunction with Oxygen / Nitride.

## Fax / Telephone Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Eduardo A. Rodela whose telephone number is (571) 272-8797. The examiner can normally be reached on M-F, 9:00AM-5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Sue Purvis can be reached on (571) 272-1236. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Eduardo A Rodela Examiner Art Unit 2826

Gal. R.

SUE A. PURVIS